| Ref # | Hits | Search Query | DBs | Default Operator | Plurals | Time Stamp |
|----------|-------|---|---|---------------------|---------|------------------|
| S1 | 62675 | SiC silicon adj carbide and colloidial adj silica | USPAT; EPO; JPO; DERWENT; IBM_TDB | OR | ON | 2005/10/13 12:03 |
| S2 | 1 | silicon adj carbide and colloidial adj silica | US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB | OR | ON | 2005/02/07 17:53 |
| S3 | 0 | cmp and colloidial adj silica | US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB | OR | ON | 2005/02/07 17:53 |
| S4 | 1 | Polishing and colloidial adj silica | US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB | OR | ON | 2005/02/07 17:54 |
| S5 | 22 | colloidial adj silica | US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB | OR | ON | 2005/02/07 18:01 |
| S6 | 2304 | polishing şame silicon adj carbide | US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB | OR | ON | 2005/02/07 18:01 |
| S7 | 963 | polishing same silicon adj carbide and semiconductor | US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB | OR | ON | 2005/02/07 18:23 |

| S8 | 94 | ("5964942" "5989755" "6140210" "6328796" "6497763" "5635269" "5676723" "6127068" "6248395" "6534228" "6150023" "5584898" "5670253" "5913974" "6284628" "6322427" "6362076" "6596610" "6720640" "5686364" "6261928" "6120353" "5582897" "5591502" "5705421" "5705423" "5744401" "5855998" "5981392" "6004866" "6117750" "6193585" "5352277" "5438951" "5500607" "5543648" "5571373" "5733177" "5736226" | US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB | OR . | ON . | 2005/02/07 18:23 |
|-----|-----|--|---|------|------|------------------|
| | | "5767691" "5776246" "5869387" "5874130" "6008128" "6051063" "6121117" "6171982" "6189546" "6230720" "6238272").pn. | | | | |
| S9 | 272 | polishing same silicon adj carbide same semiconductor | US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB | OR | ON | 2005/02/08 10:46 |
| S10 | 204 | angled ion implantation | US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB | ADJ | ON | 2005/02/07 19:08 |
| S11 | 6 | gate shadowing | US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB | ADJ | ON | 2005/02/07 19:08 |
| S12 | 47 | polishing same silicon adj carbide adj substrate | US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB | OR | ON | 2005/02/08 12:59 |
| S13 | 19 | polishing same silicon adj carbide adj substrate and diamond | US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB | OR | ON | 2005/02/08 11:30 |
| S14 | 6 | polishing same silicon adj carbide adj substrate and silica | US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB | OR | ON | 2005/02/08 10:49 |
| S15 | 2 | ("5895583").PN. | USPAT; EPO; JPO; DERWENT; IBM_TDB | OR | OFF | 2005/02/08 11:30 |

| S16 | 1 | polishing same silicon adj carbide adj substrate and oxidizing adj | US-PGPUB; USPAT; | OR | ON | 2005/02/08 13:10 |
|-----|-----|--|---|----|------|------------------|
| | | atmosphere | EPO; JPO; DERWENT; IBM_TDB | | | |
| S17 | 1 | 1996-007979.NRAN. | DERWENT | OR | OFF | 2005/02/08 13:05 |
| S18 | | polishing same silicon adj carbide adj substrate and anneal | US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB | OR | ON | 2005/02/08 13:10 |
| S19 | 69 | silicon adj carbide adj substrate and oxidizing adj atmosphere | US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB | OR | ON | 2005/02/08 14:25 |
| S20 | 11 | silicon adj carbide adj substrate same oxidizing adj atmosphere | US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB | OR | ON · | 2005/02/08 13:11 |
| S21 | 299 | silicon adj carbide adj substrate and bonded | US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB | OR | ON | 2005/02/08 14:48 |
| S22 | 441 | silicon adj carbide adj substrate and epitaxial adj growth | US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB | OR | ON | 2005/02/08 15:11 |
| S23 | 1 | silicon adj carbide adj substrate and epitaxial adj growth and polishing and oxidizing adj atmosphere | US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB | OR | ON | 2005/02/08 15:38 |
| S24 | 30 | silicon adj carbide adj substrate and epitaxial adj growth and polishing and bonding | US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB | OR | ON | 2005/02/09 10:07 |
| S25 | 4 | silicon adj carbide adj substrate same bonding and epitaxial adj growth and polishing | US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB | OR | ON | 2005/02/09 10:29 |
| S26 | 108 | silicon adj carbide adj substrate and epitaxial adj growth and bonding | US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB | OR | ON | 2005/02/09 10:16 |

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|-----|-------|--|---|----|----|------------------|
| S27 | 3 | silicon adj carbide adj substrate and epitaxial adj growth and bonding and RCA | US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB | OR | ON | 2005/02/09 10:18 |
| S28 | 15 | silicon adj carbide adj substrate same bonding and epitaxial adj growth | US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB | OR | ON | 2005/02/09 10:35 |
| S29 | 66537 | SiC silicon adj carbide and RCA SC1 | USPAT; EPO; JPO; DERWENT; IBM_TDB | OR | ON | 2005/02/17 13:33 |
| S30 | 3854 | silicon adj carbide and RCA SC1 | USPAT; EPO; JPO; DERWENT; IBM_TDB | OR | ON | 2005/02/17 13:36 |
| S31 | 1214 | silicon adj carbide and RCA SC1 and semiconductor | USPAT; EPO; JPO; DERWENT; IBM_TDB | OR | ON | 2005/02/17 13:37 |
| S32 | 1034 | silicon adj carbide adj substrate and RCA SC1 and semiconductor | USPAT; EPO; JPO; DERWENT; IBM_TDB | OR | ON | 2005/02/17 13:37 |
| S33 | 1021 | silicon adj carbide adj substrate same RCA SC1 and semiconductor | USPAT; EPO; JPO; DERWENT; IBM_TDB | OR | ON | 2005/02/17 13:38 |
| S34 | 0 | silicon adj carbide adj substrate same RCA and polishing | USPAT; EPO; JPO; DERWENT; IBM_TDB | OR | ON | 2005/02/17 13:39 |
| S35 | 0 | silicon adj carbide adj substrate same sc1 and polishing | USPAT; EPO; JPO; DERWENT; IBM_TDB | OR | ON | 2005/02/17 13:39 |
| S36 | 1 | silicon adj carbide adj substrate same HF and polishing | USPAT; EPO; JPO; DERWENT; IBM_TDB | OR | ON | 2005/02/17 13:40 |
| S37 | 0 | silicon adj carbide adj substrate same cleaning same polishing | USPAT; EPO; JPO; DERWENT; IBM_TDB | OR | ON | 2005/02/17 13:41 |
| S38 | 21 | silicon adj carbide adj substrate same cleaning andpolishing | USPAT; EPO; JPO; DERWENT; IBM_TDB | OR | ON | 2005/02/17 13:41 |

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|-----|-------|---|---|----|-----|------------------|
| S39 | 1 | silicon adj carbide adj substrate same cleaning and polishing | USPAT; EPO; JPO; DERWENT; IBM_TDB | OR | ON | 2005/02/17 13:42 |
| S40 | 6 | silicon adj carbide adj substrate same clean and polishing | USPAT; EPO; JPO; DERWENT; IBM_TDB | OR | ON | 2005/02/17 13:43 |
| S41 | 6 | silicon adj carbide adj substrate and (RCA or Hydroflouric) and polishing | USPAT; EPO; JPO; DERWENT; IBM_TDB | OR | ON | 2005/02/17 19:29 |
| S42 | 3 | silicon adj carbide adj substrate and (RCA and Hydrofluoric) and polishing | USPAT; EPO; JPO; DERWENT; IBM_TDB | OR | ON | 2005/02/17 19:29 |
| S43 | 28140 | colloidal adj silica | USPAT; EPO; JPO; DERWENT; IBM_TDB | OR | OFF | 2005/08/04 19:44 |
| S44 | 1654 | colloidal adj silica and silicon adj carbide | USPAT; EPO; JPO; DERWENT; IBM_TDB | OR | OFF | 2005/08/04 19:45 |
| S45 | 2318 | colloidal adj silica and silicon adj carbide | US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB | OR | ON | 2005/08/04 19:46 |
| S46 | 645 | colloidal adj silica and silicon adj carbide and polishing | US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB | OR | ON | 2005/08/04 19:46 |
| S47 | 143 | colloidal adj silica and silicon adj carbide and polishing and "438"/\$. ccls. | US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB | OR | ON | 2005/08/04 19:51 |
| S48 | 15 | colloidal adj silica and silicon adj carbide near5 (substrate or wafer) and polishing and "438"/\$.ccls. | US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB | OR | ON | 2005/08/04 19:52 |
| S49 | 18 | colloidal adj silica and silicon adj carbide near5 (substrate or wafer) and polishing and ("438"/\$.ccls. or "257"/\$.ccls.) | US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB | OR | ON | 2005/08/05 14:24 |

| S50 | 4 | colloidal adj silica and silicon adj carbide adj (substrate or wafer) and polishing and ("438"/\$.ccls. or "257"/\$.ccls.) | US-PGPUB; USPAT; EPO; JPO; DERWENT; | OR | ON | 2005/08/05 14:39 |
|-----|-------|---|---|------|-----|------------------|
| S51 | 290 | colloidal adj silica and surface adj roughness and ("438"/\$.ccls. or "257"/\$.ccls.) | IBM_TDB US-PGPUB; USPAT; EPO; JPO; DERWENT; | OR | ON | 2005/08/05 14:40 |
| S52 | 5 | (("5877070") or ("6833562")).PN. | IBM_TDB USPAT; EPO; JPO; DERWENT; IBM_TDB | OR . | OFF | 2005/08/05 15:57 |
| S53 | 65019 | SiC silicon adj carbide and colloidial adj silica and rms | USPAT; EPO; JPO; DERWENT; IBM_TDB | OR | ON | 2005/10/13 12:03 |
| S54 | 0 | (SiC or silicon adj carbide) and colloidial adj silica and rms | USPAT; EPO; JPO; DERWENT; IBM_TDB | OR | ON | 2005/10/13 12:04 |
| S55 | 0 | (SiC or silicon adj carbide) and colloidial adj silica and rms | US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB | OR | ON | 2005/10/13 12:05 |
| S56 | 0 | (SiC or silicon adj carbide) and colloidial adj silica and nm | US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB | OR | ON | 2005/10/13 12:05 |
| S57 | 2 | (SiC or silicon adj carbide) and colloidial adj silica | US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB | OR | ON | 2005/10/13 12:05 |
| S58 | 310 | 438/478.ccls. | USPAT; EPO; JPO; DERWENT; IBM_TDB | OR . | OFF | 2005/10/13 13:06 |
| S59 | 436 | 438/689.ccls. | USPAT; EPO; JPO; DERWENT; IBM_TDB | OR | OFF | 2005/10/13 13:21 |
| S60 | 170 | 438/478.ccls. | US-PGPUB; JPO | OR | OFF | 2005/10/13 13:07 |
| S61 | 1192 | 438/689.ccls. | US-PGPUB | OR | OFF | 2005/10/13 14:30 |
| S62 | 181 | 438/689.ccls. and slurry | US-PGPUB | OR | OFF | 2005/10/13 14:39 |
| S63 | 100 | 438/689.ccls. and slurry and silica | US-PGPUB | OR | OFF | 2005/10/13 14:39 |

| S64 | 43 | 438/689.ccls. and slurry and colloidal adj silica | US-PGPUB | OR | ON | 2005/10/13 14:43 |
|-----|-----------------|---|--|----|----|------------------|
| S65 | 20 | 438/689.ccls. and slurry and colloidal adj silica and roughness | US-PGPUB | OR | ON | 2005/10/13 14:54 |
| S66 | 3 | 438/689.ccls. and slurry and colloidal adj silica and anneal | US-PGPUB | OR | ON | 2005/10/13 14:54 |
| S67 | . 1 | 438/692.ccls. and slurry and colloidal adj silica and anneal | US-PGPUB | OR | ON | 2005/10/13 14:55 |
| S68 | 1 | 438/767.ccls. and slurry and colloidal adj silica and anneal | US-PGPUB | OR | ON | 2005/10/13 14:55 |
| S69 | 19 [.] | 438/767.ccls. | US-PGPUB | OR | ON | 2005/10/13 14:56 |
| S70 | 264 | 438/767.ccls. | USPAT; EPO; JPO; DERWENT; IBM_TDB | OR | ON | 2005/10/13 14:56 |
| S71 | 293 | 438/931.ccls. | USPAT; EPO; JPO; DERWENT; IBM_TDB | OR | ON | 2005/10/13 14:58 |